



#### 60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>C</sub> = +25°C
60V	$16m\Omega @ V_{GS} = 10V$	37A
607	$24m\Omega$ @ $V_{GS} = 4.5V$	29A

# **Description and Applications**

This MOSFET has been designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

PowerDI5060-8

- Power Management
- DC-DC Converters
- Motor Control

### **Features**

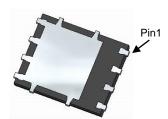
- Rated to +175°C Ideal for High Ambient Temperature Environments
- Thermally Efficient Package Cooler Running Applications
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile Ideal for Thin Applications</li>
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
  - PPAP Capable (Note 4)

## **Mechanical Data**

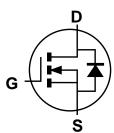
- Case: PowerDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



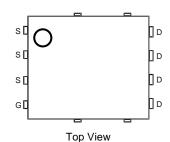




**Bottom View** 



Internal Schematic



Pin Configuration

## Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH6016LPSQ-13	PowerDI5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**

H6016LS

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PowerDI5060-8

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PowerDI is a registered trademark of Diodes Incorporated. DMTH6016LPSQ



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	60	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	37 30.3	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	T <sub>A</sub> = +25°C T <sub>A</sub> = +100°C	I <sub>D</sub>	9.8 6.9	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	75	Α	
Maximum Continuous Body Diode Forward Current (Note 7)	I <sub>S</sub>	31	Α	
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	15.3	Α	
Avalanche Energy, L = 0.1mH	Eas	11.7	mJ	

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	$P_{D}$	2.6	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	57	°C/W
Total Power Dissipation (Note 7) $T_C = +25^{\circ}C$		P <sub>D</sub>	37.5	W
Thermal Resistance, Junction to Case (Note 7)		R <sub>0JC</sub>	4	°C/W
Operating and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55 to +175	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

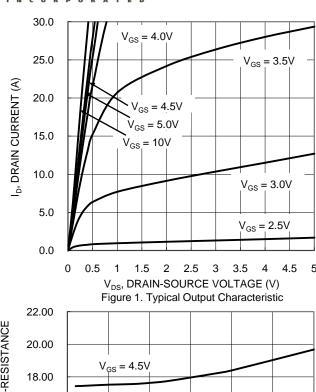
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1		2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance		_	12	16	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	21	24	11177	$V_{GS} = 4.5V, I_D = 18A$	
Diode Forward Voltage	$V_{SD}$	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	_	864	_		$V_{DS} = 30V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Output Capacitance	Coss	_	282	_	pF		
Reverse Transfer Capacitance	Crss		27	_			
Gate Resistance	Rg	_	1.3	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_g$	_	8.4	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	17	_	nC	V <sub>DS</sub> = 30V. I <sub>D</sub> = 10A	
Gate-Source Charge	$Q_{gs}$	_	3.1	_	IIC	$V_{DS} = 30V, I_D = 10A$	
Gate-Drain Charge	$Q_{gd}$	_	4.3	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.4	_			
Turn-On Rise Time	t <sub>R</sub>	_	5.2	_		$V_{GS} = 10V, V_{DS} = 30V,$ $R_{G} = 6\Omega, I_{D} = 10A$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	13	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	7	_			
Reverse Recovery Time	t <sub>RR</sub>	_	22	_	ns	1 400 4:/44 4000/	
Reverse Recovery Charge	Q <sub>RR</sub>	_	11	_	nC	I <sub>F</sub> = 10A, di/dt = 100A/μs	

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

7. Thermal resistance from junction to soldering point (on the exposed drain pad).8. Short duration pulse test used to minimize self-heating effect.

Short duration pulse test used to minimize seir-neating er
 Guaranteed by design. Not subject to product testing.





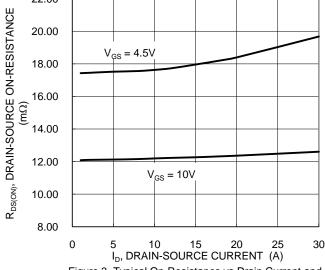


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

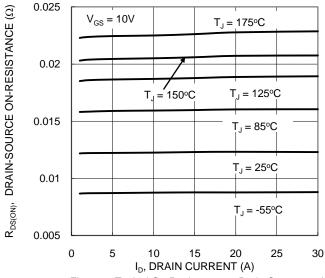


Figure 5. Typical On-Resistance vs Drain Current and **Temperature** 

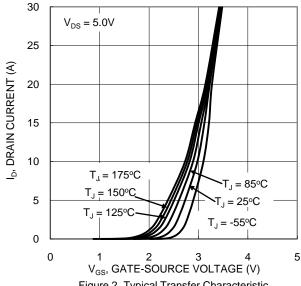
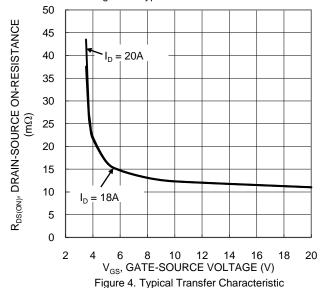


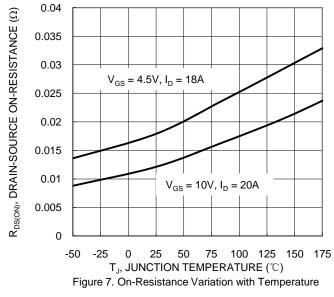
Figure 2. Typical Transfer Characteristic

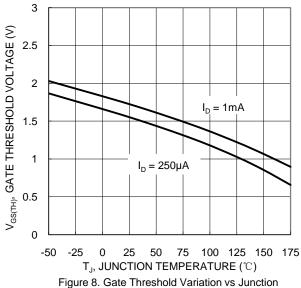


2 R<sub>DS(ON)</sub>, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED)  $V_{GS} = 10V, I_D = 20A$ 1.8 1.6 1.4 1.2 1  $V_{GS} = 4.5V, I_{D} = 18A$ 8.0 0.6 0.4 50 75 100 125 150 175 -50 -25 0 25 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

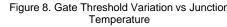
Figure 6. On-Resistance Variation with Temperature

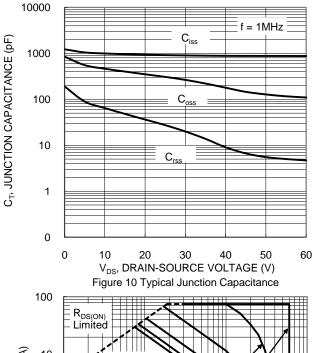


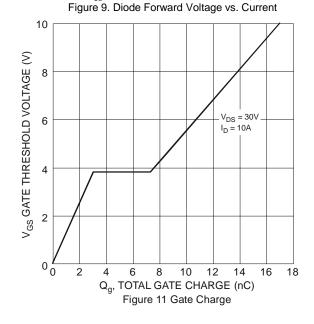


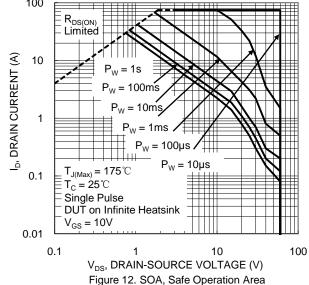


30  $V_{GS} = 0V$ 25 Is, SOURCE CURRENT (A) 20 15 10 T<sub>A</sub> = 175°C T<sub>A</sub> = 150°C  $T_A = 85^{\circ}C$ 5 T<sub>A</sub> = 25°C  $T_A = -55^{\circ}C$ 0 0 0.3 0.6 0.9 1.2 1.5 V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V)











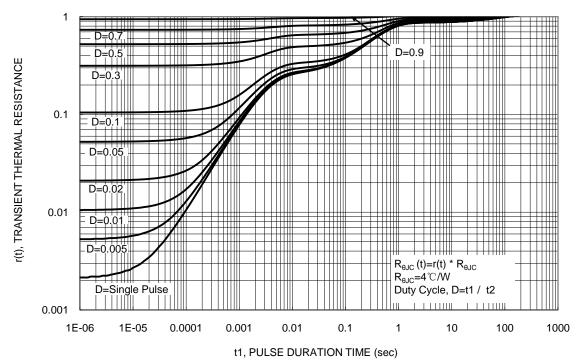


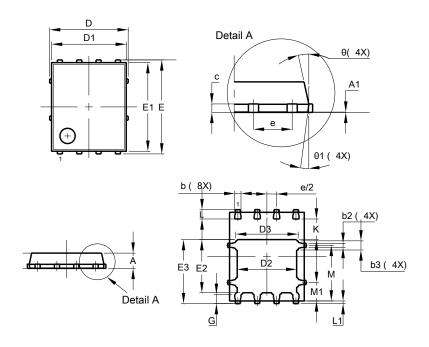
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8

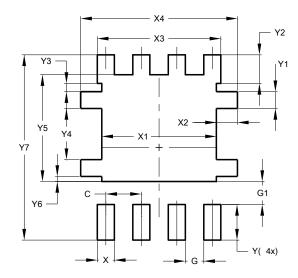


PowerDI5060-8					
Dim	Min Max		Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D		5.15 BSC			
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	(	6.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	_	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12º	11º		
Θ1	6°	8°	7º		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8



Dimensions	Value (in mm)			
C	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Υ	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
<b>Y7</b> 6.610				



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